Rev. 04/03

Docket No. ELM-1 Cont. 9

O STENIS TRADE

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant : Glenn J. Leedy

Application No.: 10/665,757 Confirmation No.: 6828

Filed : September 19, 2003

For : MEMBRANE IC FABRICATION

Group Art Unit : 2812

Examiner : Not yet assigned

New York, New York

July 2, 2004

Hon. Commissioner for Patents P.O. Box 1450 Alexandria, Virginia 22313-1450

TRANSMITTAL LETTER FOR INFORMATION DISCLOSURE STATEMENT

Sir:

Transmitted herewith is an Information Disclosure

Statement in the above-identified application. This

Statement is submitted:

- [] within three months of the application filing date;
- [X] more than three months from the application filing date but before the mailing date of the first Office Action on the merits.

In accordance with 37 C.F.R. § 1.97, submission of this Statement requires no fee. However, if for any reason a fee is due, the Director is hereby authorized to charge payment of any fees required in connection with this

Information Disclosure Statement to Deposit Account

No. 06-1075. A duplicate copy of this letter is transmitted herewith.

Respectfully submitted,

Philip R. Pol

Registration No. 51,176

Agent for Applicants

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New York, New York 10020-1105

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I hereby certify that this
Correspondence is being
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Commissioner for Patents
P.O. Box 1450

Claire J. Saintil-yan Gooding

Alexandria, VA 223131450 on

Signature of Person Signing

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicants : Glenn J. Leedy

Application No.: 10/665,757 Confirmation No.: 6828

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For : MEMBRANE IC FABRICATION

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Examiner : Not yet assigned

Hon. Commissioner for Patents

P.O. Box 1450

Alexandrian, Virginia 22313-1450

INFORMATION DISCLOSURE STATEMENT

Sir:

In accordance with 37 C.F.R. §§ 1.56 and 1.97, applicant wishes to call the attention of the Examiner to the following documents:

U.S. Patents

Fujii et al.	Re. 34,893	04/04/95
Foster	2,915,722	12/01/59
Farrand	3,202,948	08/24/65
Lesk	3,559,282	02/02/71
Burkhardt	3,560,364	02/02/71
Emmasingel	3,602,982	09/07/71
Medicus	3,615,901	10/26/71
Napoli et al.	3,716,429	02/13/73
Krishna et al.	3,777,227	12/14/73
Kuipers	3,868,565	02/25/75
Yerman	3,922,705	11/25/75
Wanlass	3,997,381	12/14/76
Stein	4,070,230	01/24/78

G	4 101 005	01/00/50
Greenwood et al.	4,131,985	01/02/79
Hauser, Jr., et al.	4,142,004	02/27/79
Hoeberechts	4,251,909	02/24/81
Kubacki	4,262,631	04/21/81
Shioya et al.	4,394,401	07/19/83
Trenkler et al.	4,401,986	08/30/83
Thomas et al.	4,416,054	11/22/83
Takagi et al.	4,539,068	09/03/85
Reid et al.	4,585,991	04/29/86
Yasumoto et al.	4,612,083	09/16/86
Belanger et al.	4,617,160	10/14/86
Shimizu et al.	4,618,397	10/21/86
Schmitz	4,618,763	10/21/86
Christensen	4,663,559	05/05/87
Burns et al.	4,684,436	08/04/87
Hatada		
	4,693,770	09/15/87
Maeda et al.	4,702,336	10/27/87
Seibert et al.	4,702,936	10/27/87
Go	4,706,166	11/10/87
Stevenson	4,721,938	01/26/88
Reid	4,761,681	08/02/88
Holmen et al.	4,784,721	11/15/88
Freeman	4,810,673	03/07/89
Mattox et al.	4,825,277	04/25/89
Tam et al.	4,857,481	08/15/89
Leedy	4,924,589	05/15/90
Borel et al.	4,940,916	07/10/90
Borel et al.	ReB14,940916	11/26/96
Vranish et al.	4,950,987	08/21/90
Lee et al.	4,952,446	08/18/90
Rokos	4,954,865	09/04/90
Shinomiya	4,957,882	09/18/90
Young et al.	4,965,415	10/23/90
		10/23/90
Mauger	4,966,663	
Leedy	4,994,735	02/19/91
Keogh et al.	5,008,619	04/16/91
Allen et al.	5,010,024	04/23/91
Leedy	5,020,219	06/04/91
Leedy	5,034,685	07/23/91
Greenwald et al.	5,070,026	12/03/91
Findler et al.	5,071,510	12/10/91
Machado et al.	5,098,865	03/24/92
Leedy	5,103,557	03/24/92
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Mauger	5,110,373	05/05/92
Eichelberger	5,111,278	05/05/92
Chan et al.	5,116,777	05/26/92
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Desc	5 130 044	07/01/00
Roy	5,132,244	07/21/92
Hadwin	5,151,775	09/29/92
Henager, Jr., et al	.5,156,909	10/20/92
Zimmerman	5,203,731	04/20/93
Leedy	5,225,771	07/06/93
_		• •
Bower et al.	5,236,118	08/17/93
Bureau et al.	5,262,351	11/16/93
Bertin et al.	5,270,261	12/14/93
Sanders	5,273,940	12/28/93
Tuckerman	5,274,270	12/28/93
Chebi et al.	5,279,865	01/18/94
Nakanishi et al.	5,284,796	02/08/94
Leedy	5,323,035	06/21/94
Wojnarowski	5,324,687	06/28/94
Leedy	5,354,695	10/11/94
MacDonald	5,363,021	11/08/94
Goossen	5,385,632	01/31/95
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Shimoji	5,420,458	05/30/95
-		
Miyake	5,424,920	06/13/95
Finnila	5,426,072	06/20/95
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Leedy	5,451,489	09/19/95
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Gurtler et al.	5,457,879	10/17/95
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Pati et al.	5,527,645	06/18/96
Koskenmaki et al.	5,529,829	06/25/96
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Leedy		•
-	5,580,687	12/03/96
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	5,606,186	02/25/97
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Val	5,637,536	06/10/97
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Weise et al.	5,750,211	05/12/98
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Okonogi	5,773,152	06/30/98
Rolfson	5,786,116	07/28/98
Zavracky et al.	5,793,115	08/11/98
Ray	5,831,280	11/03/98
Leedy	5,834,334	11/10/98
Leedy	5,840,593	11/24/98
Ito et al.	5,856,695	01/05/99
Sotokawa et al.	5,868,949	02/09/99
Leedy	5,869,354	02/09/99
Sweatt et al.	5,870,176	02/09/99
Davidson	5,880,010	03/09/99
Field et al.	5,882,532	03/16/99
Hübner	5,902,118	05/11/99
Leedy	5,915,167	06/22/99
Leedy	5,946,559	08/31/99
Leedy	5,985,693	11/16/99
Cutter et al.	5,998,069	12/07/99
Leedy	6,008,126	12/28/99
Leedy	6,020,257	02/01/00
Houston	6,045,625	04/04/00
Adamic, Jr.	6,084,284	07/04/00
Gardner et al.	6,097,096	08/01/00
Leedy	6,133,640	10/17/00
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Aleshin et al.	6,197,456 B1	03/06/01
Leedy	6,208,545 B1	03/27/01
Patti	6,236,602 B1	05/22/01
Lin	6,261,728 B1	07/17/01
Leedy	6,288,561 B1	09/11/01
Leedy	6,294,909 B1	09/11/01

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JAPAN	JP 04-083371	03/1992
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Other Documents

"IC Tower Patent: Simple Technology Receives Patent on the IC Tower, a Stacked Memory Technology," http://www.simpletech.com/whatsnew/memory/@60824.htm (1998).

Alloert, K., et al., "A Comparison Between Silicon Nitride Films Made by PCVD of N_2 -SiH₄ /A_r and N_2 -SiH₄/He," Journal of the Electrochemical Society, Vol. 132, No. 7, pp. 1763-1766, (July 1985).

Hendricks, et al., "Polyquinoline Coatings and Films: Improved Organic Dielectrics for IC's and MCM's," Eleventh IEEE/CHMT International Electronics Manufacturing Technology Symposium," pp. 361-265 (1991).

Knolle, W.R., et al., "Characterization of Oxygen-Doped, Plasma-Deposited Silicon Nitride," Journal of the Electrochemical Society, Vol. 135, No. 5, pp. 1211-1217, (May 1988).

Nguyen, S.V., "Plasma Assisted Chemical Vapor Deposited Thin Films for Microelectronic Applications, J. Vac. Sci. Technol. Vol. B4, No. 5, pp.1159-1167, (Sep/Oct. 1986).

Olmer, et al., "Intermetal Dielectric Deposition by Plasma Enhanced Chemical Vapor Deposition," Fifth IEEE/CHMT International Electronic Manufacturing Technology Symposium - Design-to-Manufacturing Transfer Cycle," pp. 98-99 (1988).

Runyan, W.R., "Deposition of Inorganic Thin Films," Semiconductor Integrated Circuit Processing Technology, p. 142 (1990).

Sze, S.M., "Surface Micromachining," Semiconductor Sensors, pp. 58-63 (1994).

Vossen, John L., "Plasma-Enhanced Chemical Vapor Deposition," Thin Film Processes II, pp. 536-541 (1991).

Wolf, Stanley, "Basic of Thin Films," Silicon Processing for the VLSI Era, pp. 115, 192-193 and 199 (1986).

Copies of the aforementioned documents are listed on the accompanying Form PTO-1449 (submitted in duplicate).

It is respectfully requested that these documents be:

(1) fully considered by the Patent and Trademark Office

during the examination of this application; and (2) printed

on any patent which may issue on this application.

Applicant requests that a copy of Form PTO-1449, as

considered and initialized by the Examiner, be returned with

the next communication.

Consideration of the foregoing in relation to this patent application is respectfully requested.

Respectfully submitted,

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Objection of the miss."
Ported Section 11 thanks

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Addressed for

Commiscian - fat Patants

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Signature of Person Signing

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FORM PTO-1449

U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE

INFORMATION DISCLOSURE STATEMENT BY APPLICANT

_		
	ATTY. DOCKET NO. ELM-1 Cont. 9	APPLICATION NO. 10/665,757
	APPLICANT Glenn J. Leedy	CONFIRMATION NO. 6828
	FILING DATE September 19, 2003	GROUP 2812

U.S. PATENT DOCUMENTS

EXAMINE R INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
	Re. 34,893	04/04/95	Fujii et al.	257	419	ALLICOTUALE
	2,915,722	12/01/59	Foster	336	115	
	3,202,948	08/24/65	Farrand	336	115	
	3,559,282	02/02/71	Lesk	438	113	
	3,560,364	02/02/71	Burkhardt	324	207.12	
	3,602,982	09/07/71	Emmasingel	29	577	
	3,615,901	10/26/71	Medicus	148	11.5 R	<u> </u>
	3,716,429	02/13/73	Napoli et al.	156	17	
· · · · · · · · · · · · · · · · · · ·	3,777,227	12/14/73	Krishna et al.	257	578	
	3,868,565	02/25/75	Kuipers	324	207.26	
	3,922,705	11/25/75	Yerman	357	26	
··	3,997,381	12/14/76	Wanlass	156	3	
_	4,070,230	01/24/78	Stein	156	657	
	4,131,985	01/02/79	Greenwood et al.	29	580	
	4,142,004	02/27/79	Hauser, Jr. et al.	438	792	·
· · · · · · · · · · · · · · · · · · ·	4,251,909	02/24/81	Hoeberechts	29	580	
	4,262,631	04/21/81	Kubacki	118	723MP	
	4,394,401	07/19/83	Shioya et al.	427	574	
· · · · · · · · · · · · · · · · · · ·	4,401,986	08/30/83	Trenkler et al.	340	870.32	
	4,416,054	11/22/83	Thomas et al.	29	572	
	4,539,068	09/03/85	Takagi et al.	156	614	
	4,585,991	04/29/86	Reid et al.	324	158 P	
	4,612,083	09/16/86	Yasumoto et al.	156	633	
	4,617,160	10/14/86	Belanger et al.	264	40.1	
	4,618,397	10/21/86	Shimizu et al.	156	628	
	4,618,763	10/21/86	Schmitz	250	211R	
	4,663,559	05/05/87	Christensen	313	336	
	4,684,436	08/04/87	Burns et al.	216	65	
	4,693,770	09/15/87	Hatada	156	151	•

EXAMINER

FORM PTO-1449			OF COMMERCE DEMARK OFFICE	ATTY. D ELM-1 C	OCKET NO.	APPLICATION NO. 10/665,757	
	FORMATION				APPLICANT CONFIRMATION 6828		
	STATEMENT B			FILING DATE September 19, 2003		GROUP 2812	
4,702,	336	10/27/87	Maeda et al.	180	197		
4,702,		10/27/87	Seibert et al.	427	583		
4,706,	166	11/10/87	Go	361	403		
4,721,		01/26/88	Stevenson	338	4		
4,761,	681	08/02/88	Reid	357	68		
4,784,	721	11/15/88	Holmen et al.	156	647		
4,810,		03/07/89	Freeman	438	386		
4,825,	277	04/25/89	Mattox et al.	257	639		
4,857,	481	08/15/89	Tam et al.	438	619		
4,924,	589	05/15/90	Leedy	438	6		
4,940,	916	07/10/90	Borel et al.	313	306		
Re B1	4,940,916	11/26/96	Borel et al.	315	306		
4,950,	987	08/21/90	Vranish et al.	324	207.23		
4,952,	446	08/18/90	Lee et al.	428	220	-	
4,954,	865	09/04/90	Rokos	257	378		
4,957,	882	09/18/90	Shinomiya	438	65		
4,965,	415	10/23/90	Young et al.	200	83 N		
4,966,	663	10/30/90	Mauger	205	656		
4,994,	735	02/19/91	Leedy	324	158		
5,008,	619	04/16/91	Keogh et al.	324	207.17		
5,010,	024	04/23/91	Allen et al.	438	659		
5,020,	219	06/04/91	Leedy	29	846		
5,034,	685	07/23/91	Leedy	324	158 F		
5,070,	026	.12/03/91	Greenwald et al.	437	3		
5,071,	510	12/10/91	Findler et al.	156	647		
5,098,	865	03/24/92	Machado et al.	438	788		
5,103,	557	04/14/92	Leedy	29	832		
5,110,	373	05/05/92	Mauger	148	33.2		
5,111,	278	05/05/92	Eichelberger	357	75		
5,116,		05/26/92	Chan et al.	438	234		
5,130,	894	07/14/92	Miller	361	393		
5,132,	244	07/21/92	Roy	438	477		

FORM PTO-1449		NT OF COMMERCE ADEMARK OFFICE	ATTY. DOC ELM-1 Cont		APPLICATION NO. 10/665,757
	FORMATION DISCLO TATEMENT BY APPL		APPLICANT CONF Glenn J. Leedy 6828		CONFIRMATION NO. 6828
		IOAN	FILING DAT September		GROUP 2812
					<u> </u>
5,151,	775 09/29/92	Hadwin	357	80	
5,156,	909 10/20/92	Henager, Jr. et al.	428	334	
5,203,	731 04/20/93	Zimmerman	445	24	
5,225,	771 07/06/93	Leedy	324	158	
5,236,	118 08/17/93	Bower et al.	228	193	
5,262,	351 11/16/93	Bureau et al.	437	183	
5,270,	261 12/14/93	Bertin et al.	437	209	
5,273,	940 12/28/93	Sanders	437	209	
5,274,	270 12/28/93	Tuckerman	257	758	
5,279,	865 01/18/94		427	574	
5,284,	796 02/08/94	Nakanishi et al.	437	183	
5,323,0	035 06/21/94	Leedy	257	48	
5,324,	687 06/28/94		437	225	
5,354,	695 10/11/94		438	411	
5,363,	021 11/08/94		315	366	
5,385,	632 01/31/95	Goossen	156	630	
5,385,	909 01/31/95	Nelson et al.	514	291	
5,420,4	458 05/30/95	Shimoji	257	622	
5,424,	920 06/13/95		361	735	
5,426,0	072 06/20/95		437	208	
5,426,	363 06/20/95	Akagi et al.	324	239	
5,432,	444 07/11/95		324	240	
5,432,			365	63	
5,434,			324	67	
5,451,			430	313	
5,453,	***************************************		437	203	
5,457,		***	29	895	
5,476,		· · · · · · · · · · · · · · · · · · ·	437	132	
5,489,			437	208	
5,502,			365	51	
5,512,			430	30	
5,527,			430	5	

FORM PTO-1449		NT OF COMMERCE ADEMARK OFFICE	ATTY. DOC ELM-1 Cont		APPLICATION NO. 10/665,757	
	FORMATION DISCLO		APPLICANT Glenn J. Led	CONFIRMATION NO. 6828		
		IOAN	FILING DAT September		GROUP 2812	
5,529,	329 06/25/96	Koskenmaki et al.	428	167		
5,534,	465 07/09/96	Frye et al.	437	209		
5,555,	212 09/10/96	Toshiaki et al.	365	200		
5,563,	084 10/08/96	Ramm et al.	437	51		
5,571,	741 11/05/96	Leedy	437	51		
5,580,	687 12/03/96	Leedy	430	5		
5,581,	498 12/03/96	Ludwig et al.	365	63		
5,582,	939 12/10/96	Pierrat	430	5		
5,583,	688 12/10/96	Hornbeck	359	291		
5,592,	007 01/07/97	Leedy	257	347		
5,592,	018 01/07/97	Leedy	257	619		
5,595,	933 01/21/97	Heijboer	439	20		
5,606,	186 02/25/97	Noda	257	226		
5,627,	112 05/06/97	Tennant et al.	438	113		
5,629,	137 05/13/97	Leedy	430	313		
5,633,	209 05/27/97		435	228		
5,637,	536 06/10/97		438	686		
5,654,	127 08/05/97	Leedy	430	315		
5,654,	220 08/05/97	Leedy	438	25		
5,656,		Hudak et al.	438	15		
5,675,	185 10/07/97	Chen et al.	257	774		
5,694,	588 12/02/97	Ohara et al.	395	566		
5,725,			430	315		
5,750,		i i	427	579		
5,760,	478 06/02/98		257	777		
5,773,			428	446		
5,786,			430	5		
5,793,			257	777		
5,831,			257	48		
5,834,			438	107		
5,840,			438	6		
5,856,	1		257	370		

FORM PTO-1	FORM PTO-1449 U.S. DEPAR PATENT AN					ATTY. DOCKET NO. APPLICATION I ELM-1 Cont. 9 10/665,757			1 NO.	
	INFORMATIC STATEMENT							CON 6828	CONFIRMATION NO. 828	
	STATEMENT	- DI AFI	PLIC.	AN I	:	FILING DAT September		GRO 2812		
	5,868,949	02/09/9	99	Sotokaw	a et al.	216	18			
	5,869,354	02/09/9			438	110				
	5,870,176	02/09/9		Sweatt e	t al.	355	53			
	5,880,010	03/09/9		Davidsor		438	455			
	5,882,532	03/16/9	$\overline{}$	Field et a		216	2			
	5,902,118	05/11/9		1		438	106			
	5,915,167	06/22/9	99 Leedy		438	108				
	5,946,559	08/31/			438	157				
	5,985,693	11/16/	/99 Leedy		438	107				
	5,998,069	12/07/			430	5				
	6,008,126 12/28			99 Leedy		438	667			
	6,020,257 02/01			Leedy		438	626			
	6,045,625 04/04		00 Houston		148	33.3				
	6,084,284 07/0		00 Adamic, Jr.		257	506				
	6,097,096	08/01/	7/00 Gardner et al. 7/00 Leedy 7/01 Tayanaka		et al.	257	777			
	6,133,640	10/17/			Leedy		778			
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